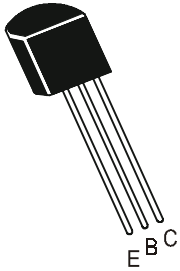


**NPN EPITAXIAL PLANAR SILICON HIGH VOLTAGE TRANSISTOR**

**2N5550**



**TO-92  
Plastic Package**

**High Voltage NPN Transistor For General Purpose and Telephony Applications.**

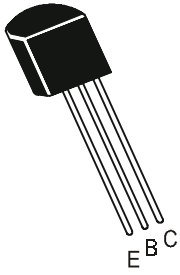
**ABSOLUTE MAXIMUM RATINGS(Ta=25°C unless specified otherwise)**

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	$V_{CEO}$	140	V
Collector Base Voltage	$V_{CBO}$	160	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current Continuous	$I_C$	600	mA
Power Dissipation@ Ta=25°C	$P_D$	625	mW
Derate Above 25°C		5.0	mW/°C
Power Dissipation@ Tc=25°C	$P_D$	1.5	W
Derate Above 25°C		12	mW/°C
Operating And Storage Junction Temperature Range	$T_j, T_{stg}$	-55 to +150	°C

**THERMAL RESISTANCE**

Junction to ambient	$R_{th(j-a)} (1)$	357	°C/W
Junction to case	$R_{th(j-c)}$	125	°C/W

**(1) Rth (j-a) is measured with the device soldered into a typical printed circuit board**

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)**

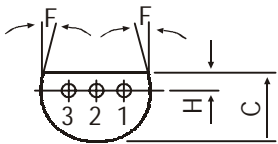
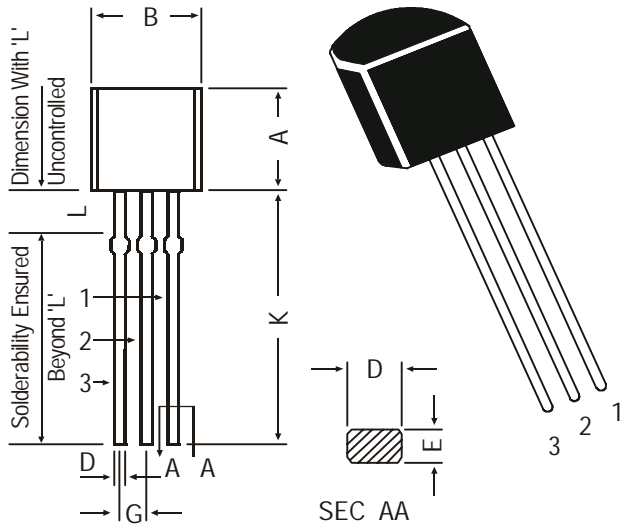
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Base Voltage	$V_{CE0}^*$	$I_C=1mA, I_B=0$	140			V
Collector Base Voltage	$V_{CBO}$	$I_C=100\mu A, I_E=0$	160			V
Emitter Base Voltage	$V_{EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector Cut off Current	$I_{CBO}$	$V_{CB}=100V, I_E=0$			100	nA
		$T_a=100^\circ C$ $V_{CB}=100V, I_E=0$			100	$\mu A$
Emitter Cut off Current	$I_{EBO}$	$V_{BE}=4V, I_C=0$			50	nA
						$\mu A$
DC Current Gain	$h_{FE}^*$	$V_{CE}=5V, I_C=1mA$	60			
		$V_{CE}=5V, I_C=10mA$	60		250	
		$V_{CE}=5V, I_C=50mA$	20			
Base Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C=10mA, I_B=1mA$			1.0	V
		$I_C=50mA, I_B=5mA$			1.2	V
Collector Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C=10mA, I_B=1mA$			0.15	V
		$I_C=50mA, I_B=5mA$			0.25	V

**DYNAMIC CHARACTERISTICS**

Small Signal Current Gain	hfe	$I_C=1mA, V_{CE}=10V$ $f=1KHz$	50		200	
Transition Frequency	$f_T$	$I_C=10mA, V_{CE}=10V$ $f=100MHz$	100		300	MHz
Output Capacitance	$C_{obo}$	$I_E=0, V_{CB}=10V$ $f=1MHz$			6.0	pF
Input Capacitance	$C_{ibo}$	$I_C=0, V_{EB}=0.5V$ $f=1MHz$			30	pF
Noise Figure	NF	$V_{CE}=5V, I_C=250\mu A$ $R=1\Omega, f=10Hz$ to 15.7kHz			10	dB

\*Pulse Condition: Width = 300 $\mu s$ , Duty Cycle= 2%.

TO-92 Plastic Package



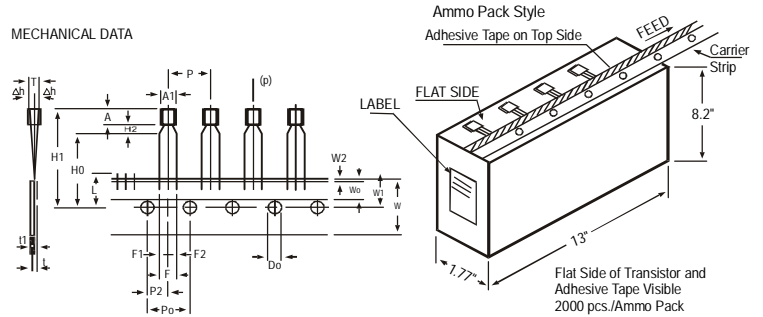
PIN CONFIGURATION

1. COLLECTOR
2. BASE
3. EMITTER

DIM	MIN.	MAX.
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5 DEG	
G	1.14	1.40
H	1.14	1.53
K	12.70	—
L	1.982	2.082

All dimensions in mm.

TO-92 Transistors on Tape and Ammo Pack



All dimensions in mm unless specified otherwise

ITEM	SYMBOL	SPECIFICATION				REMARKS
		MIN.	NOM.	MAX.	TOL.	
BODY WIDTH	A1	4.0		4.8		
BODY HEIGHT	A	4.8		5.2		
BODY THICKNESS	T	3.9		4.2		
PITCH OF COMPONENT	P		12.7		±1	
FEED HOLE PITCH	Po		12.7		±0.3	CUMULATIVE PITCH ERROR 1.0 mm/20 PITCH
FEED HOLE CENTRE TO COMPONENT CENTRE	P2		6.35		±0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER LEADS	F		5.08		+0.6 -0.2	
COMPONENT ALIGNMENT	Δh		0	1		AT TOP OF BODY
TAPE WIDTH	W		18		±0.5	
HOLD-DOWN TAPE WIDTH	Wo		6		±0.2	
HOLE POSITION	W1		9		+0.7 -0.5	
HOLD-DOWN TAPE POSITION	W2		0.5		±0.2	
LEAD WIRE CLINCH HEIGHT	Ho		16		±0.5	
COMPONENT HEIGHT	H1			23.25		
LENGTH OF SNIPPED LEADS	L			11.0		
FEED HOLE DIAMETER	Do		4		±0.2	
TOTAL TAPE THICKNESS	t			1.2		1) 0.3 - 0.6
LEAD - TO - LEAD DISTANCE F1,	F2		2.54		+0.4 -0.1	
CLINCH HEIGHT	H2			3		
PULL - OUT FORCE	(P)		6N			

NOTES

1. MAXIMUM ALIGNMENT DEVIATION BETWEEN LEADS NOT TO BE GREATER THAN 0.2 mm.
2. MAXIMUM NON-CUMULATIVE VARIATION BETWEEN TAPE FEED HOLES SHALL NOT EXCEED 1 mm IN 20 PITCHES.
3. HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO EXPOSURE OF ADHESIVE.
4. NO MORE THAN 3 CONSECUTIVE MISSING COMPONENTS ARE PERMITTED.
5. A TAPE TRAILER, HAVING AT LEAST THREE FEED HOLES ARE REQUIRED AFTER THE LAST COMPONENT.
6. SPLICES SHALL NOT INTERFERE WITH THE SPROCKET FEED HOLES.

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2K	17" x 15" x 13.5"	32K	12.5 kgs

### **Disclaimer**

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